

December 2014

FCH104N60F

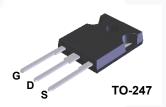
N-Channel SuperFET[®] II FRFET[®] MOSFET 600 V, 37 A, 104 m Ω

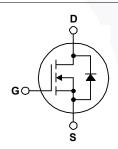
Features

- 650 V @ T_J = 150°C
- Typ. $R_{DS(on)}$ = 98 m Ω
- Ultra Low Gate Charge (Typ. Q_q = 107 nC)
- Low Effective Output Capacitance (Typ. C_{oss(eff.)} = 109 pF)
- · 100% Avalanche Tested
- · RoHS Compliant

Description

SuperFET® II MOSFET is Fairchild Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET II MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications. SuperFET II FRFET® MOSFET's optimized body diode reverse recovery performance can remove additional component and improve system reliability.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter		FCH104N60F	Unit	
V_{DSS}	Drain to Source Voltage			600	V	
V	Gate to Source Voltage	- DC		±20	V	
V_{GSS}	Gate to Source voltage	- AC	(f > 1 Hz)	±30	V	
	Drain Current	- Continuous (T _C = 25°C)		37	А	
D	Dialii Current	- Continuous (T _C = 100°C)		24	A	
I _{DM}	Drain Current	- Pulsed	(Note 1)	111	Α	
E _{AS}	Single Pulsed Avalanche Energ	ЭУ	(Note 2)	809	mJ	
I _{AR}	Avalanche Current		(Note 1)	6.8	Α	
E _{AR}	Repetitive Avalanche Energy		(Note 1)	3.57	mJ	
dv/dt	MOSFET dv/dt			100	V/ns	
uv/ut	Peak Diode Recovery dv/dt		(Note 3)	50	V/IIS	
Б	Dower Dissipation	$(T_C = 25^{\circ}C)$		357	W	
P_D	Power Dissipation	- Derate Above 25°C		2.85	W/°C	
T _J , T _{STG}	Operating and Storage Temper	ature Range		-55 to +150	°C	
T _L	Maximum Lead Temperature for	or Soldering, 1/8" from Case for 5 Sec	onds	300	°C	

Thermal Characteristics

Symbol	Parameter	FCH104N60F	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.35	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	- 0/00

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCH104N60F	FCH104N60F	TO-247	Tube	N/A	N/A	30 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Chara	cteristics					
D\/	Drain to Source Breakdown Voltage	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}, T_C = 25^{\circ}\text{C}$	600	-	-	V
BV _{DSS}	Dialii to Source Breakdown Voltage	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}, T_C = 150^{\circ}\text{C}$	650	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 10 mA, Referenced to 25°C	-	0.67	-	V/°C
1	Zero Gate Voltage Drain Current	V _{DS} = 600 V, V _{GS} = 0 V	-	-	10	
IDSS	Zero Gate voltage Drain Current	$V_{DS} = 480 \text{ V}, V_{GS} = 0 \text{ V}, T_{C} = 125^{\circ}\text{C}$	C - 16	-	μА	
I _{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	ı	-	±100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	3	-	5	V
R _{DS(on)}	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 18.5 \text{ A}$	-	98	104	mΩ
9 _{FS}	Forward Transconductance	$V_{DS} = 20 \text{ V}, I_{D} = 18.5 \text{ A}$	-	47	1	S

Dynamic Characteristics

C _{iss}	Input Capacitance	., ,,,,,,	-	4475	5950	pF
C _{oss}	Output Capacitance	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1 MHz		135	180	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 101112	- \	1.5	2.5	pF
C _{oss}	Output Capacitance	V _{DS} = 380 V, V _{GS} = 0V, f = 1 MHz	-	75	-	pF
C _{oss(eff.)}	Effective Output Capacitance	V _{DS} = 0 V to 480 V, V _{GS} = 0 V	-	109	-	pF
Q _{g(tot)}	Total Gate Charge at 10V	V _{DS} = 380 V, I _D = 18.5 A,	-	107	139	nC
Q_{gs}	Gate to Source Gate Charge	V _{GS} = 10 V	-	25	-	nC
Q_{gd}	Gate to Drain "Miller" Charge	(Note 4)	-	44	-	nC
ESR	Equivalent Series Resistance	f = 1 MHz	-	0.87	-	Ω

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		-/	34	78	ns
t _r		$V_{DD} = 380 \text{ V}, I_D = 18.5 \text{ A},$	-	24	58	ns
t _{d(off)}	Turn-Off Delay Time	$V_{GS} = 10 \text{ V}, R_{G} = 4.7 \Omega$ (Note 4)	/-	98	206	ns
t _f	Turn-Off Fall Time	(14016 4)	/ · -	5	20	ns

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current			-	37	Α
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	111	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 18.5 A	-	-	1.2	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 18.5 A,	-	144	-	ns
Q _{rr}	Reverse Recovery Charge	$dI_F/dt = 100 A/\mu s$	-	0.91	//-	μС

Notes

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. I_{AS} = 6.8 A, R_{G} = 25 Ω , starting T_{J} = 25°C.
- 3. $I_{SD} \le$ 18.5 A, di/dt \le 200 A/ μ s, $V_{DD} \le$ 380 V, starting T_J = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

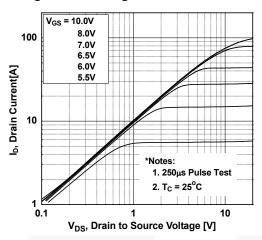


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

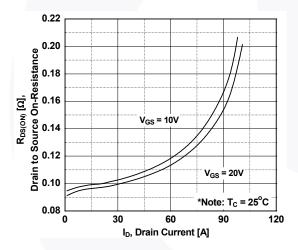


Figure 5. Capacitance Characteristics

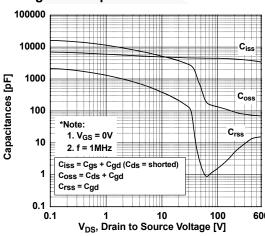


Figure 2. Transfer Characteristics

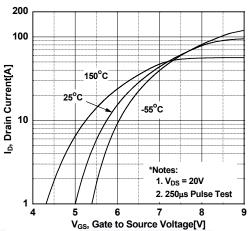


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

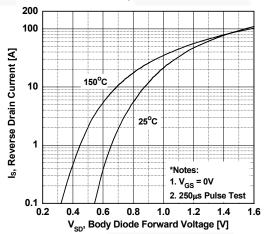
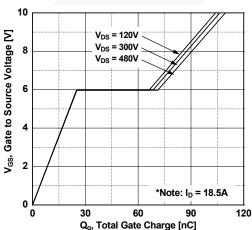


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

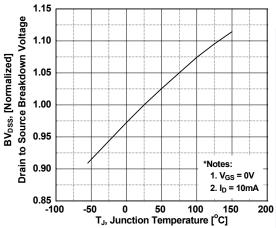


Figure 9. Maximum Safe Operating Area

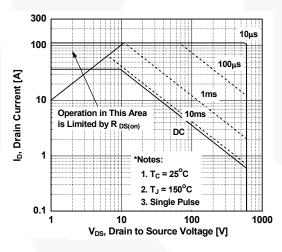


Figure 11. Eoss vs. Drain to Source Voltage

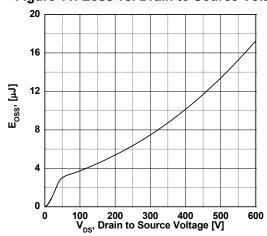


Figure 8. On-Resistance Variation vs. Temperature

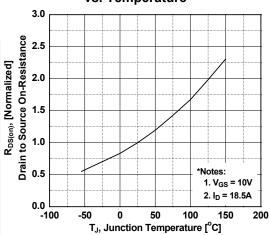
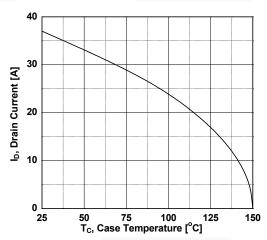
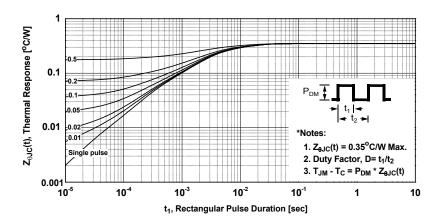


Figure 10. Maximum Drain Current vs. Case Temperature



Typical Performance Characteristics (Continued)





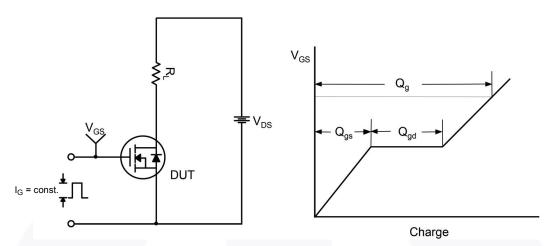


Figure 13. Gate Charge Test Circuit & Waveform

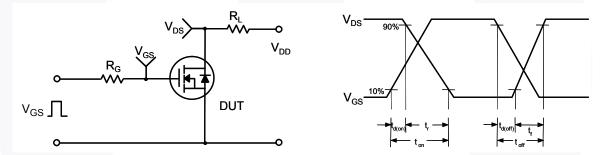


Figure 14. Resistive Switching Test Circuit & Waveforms

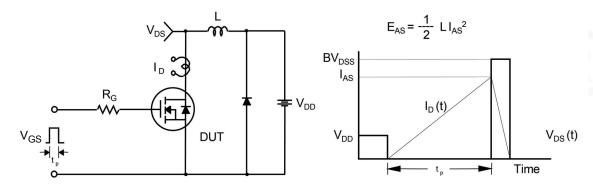


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

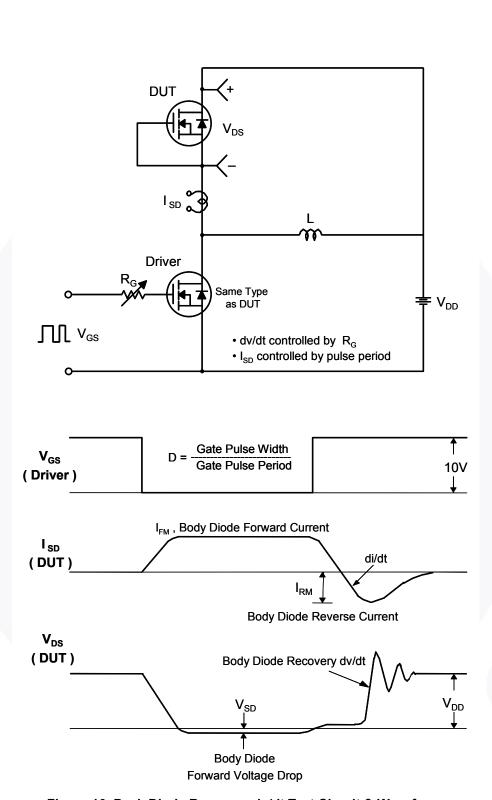
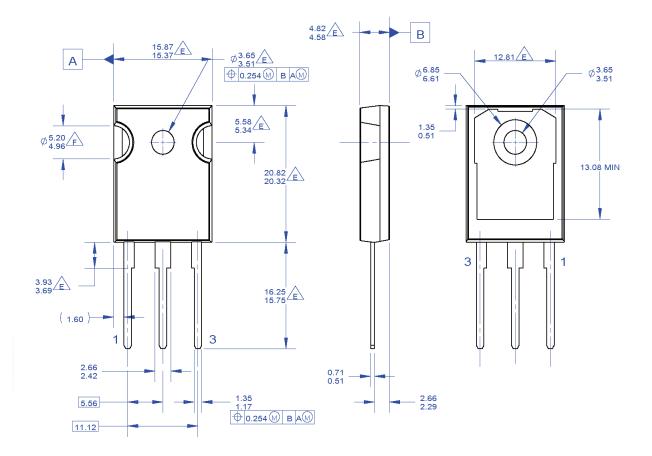


Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions



NOTES: UNLESS OTHERWISE SPECIFIED

- A. PACKAGE REFERENCE: JEDEC TO-247,
- ISSUE E, VARIATION AB, DATED JUNE, 2004.
 B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD
- FLASH, AND TIE BAR EXTRUSIONS.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DRAWING CONFORMS TO ASME Y14.5 1994
- DOES NOT COMPLY JEDEC STANDARD VALUE
- F NOTCH MAY BE SQUARE
- G. DRAWING FILENAME: MKT-TO247A03_REV03

Figure 17. TO-247, Molded, 3-Lead, Jedec Variation AB

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